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U.S. UTILITY Patent Application

PATENT NUMBER and
ISSUE DATE

APPL NUM 10041026	FILING DATE 12/28/2001	CLASS 118	SUBCLASS	GAU 1734	EXAMINER Meeky
**APPLICANTS: Subramony Janardhanan; Yokota Yoshitaka; Iyer Ramaseshan; Luo Lee; Chen Aihua; 1762					
**CONTINUING DATA VERIFIED:					
** FOREIGN APPLICATIONS VERIFIED:					
PG-PUB <input type="checkbox"/> DO NOT PUBLISH <input type="checkbox"/>		RESCIND <input type="checkbox"/>			
Foreign priority claimed <input type="checkbox"/> yes <input type="checkbox"/> no 35 USC 119 conditions met <input type="checkbox"/> yes <input type="checkbox"/> no Verified and Acknowledged Examiners's initials				ATTORNEY DOCKET NO 006333	
TITLE : Methods for silicon oxide and oxynitride deposition using single wafer low pressure CVD <small>U.S. DEPT. OF COMM./PAT. & TM-PTO-436L (Rev. 12-94)</small>					

NOTICE OF ALLOWANCE MAILED		Assistant Examiner	CLAIMS ALLOWED	
			Total Claims	Print Claim for O.G.
ISSUE FEE		Primary Examiner	DRAWING	
Amount Due	Date Paid		Sheets Drwg.	Figs. Drwg.
<input type="checkbox"/> TERMINAL DISCLAIMER		PREPARED FOR ISSUE	Application Examiner	
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